



### 30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

90 A

#### **Features**

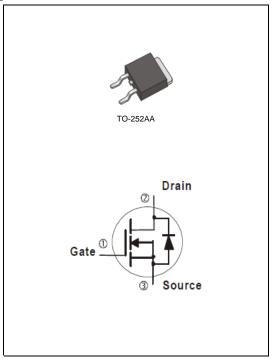
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V,I<sub>D</sub>@20A<2.6mΩ</li>
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V,I<sub>D</sub>@15A<3.4mΩ</li>
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

#### **Mechanical Data**

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



# $\textbf{Maximum Ratings and Thermal Characteristics} \; (T_{\text{A}} = 25 ^{\circ} \text{C unless otherwise noted})$

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	l <sub>D</sub>	90	А	
	T <sub>C</sub> =100°C		57		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	360		
Power Dissipation	T <sub>C</sub> =25°C	Po	100	W	
	T <sub>C</sub> =100°C		40		
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	20	^	
	T <sub>A</sub> =70°C		16	А	
Power Dissipation	T <sub>A</sub> =25°C	D	2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	180	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.25	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.6	2.5			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =20A	-	1.9	2.6	mΩ		
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =15A	-	2.4	3.4			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V	-	-	1	uA		
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 7)	Dynamic (Note 7)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =15V, I <sub>D</sub> =24A, V <sub>GS</sub> =4.5V (Note 2,3)	-	35	-	nC		
Gate-Source Charge	$Q_gs$		-	13	-			
Gate-Drain Charge	$Q_{gd}$		-	10	-			
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	4305	-	pF		
Output Capacitance	Coss		-	617	-			
Reverse Transfer Capacitance	Crss	I=1.UIVIHZ	-	310	-			
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/  40	-	13	-			
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}=15V,I_{D}=1A,$ $V_{GS}=10V,R_{G}=1\Omega$ (Note 2,3)	-	14	-	ns		
Turn-Off Delay Time	td <sub>(off)</sub>		ı	46	-			
Turn-Off Fall Time	t <sub>f</sub>	, , ,	ı	32	-			
Drain-Source Diode								
Maximum Continuous Drain-Source			-	-	90	А		
Diode Forward Current	I <sub>S</sub>							
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.66	1.0	V		

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =60A,  $V_{DD}$ =25V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

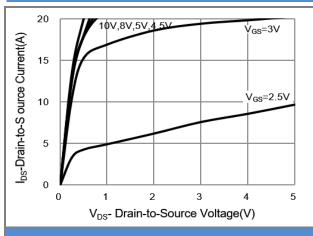


Fig.1 Output Characteristics

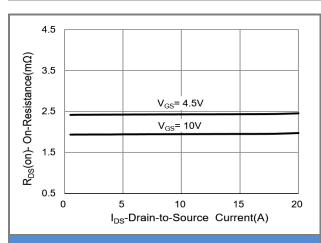


Fig.3 On-Resistance vs. Drain Current

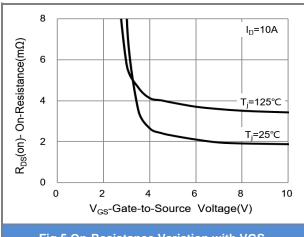
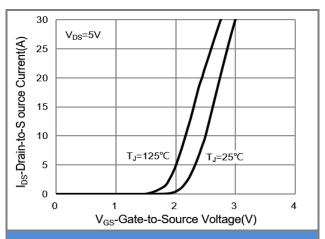


Fig.5 On-Resistance Variation with VGS.



**Fig.2 Transfer Characteristics** 

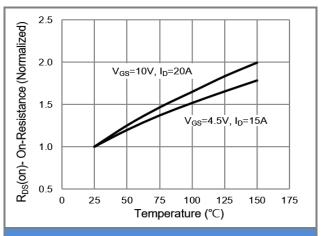


Fig.4 On-Resistance vs. Junction temperature

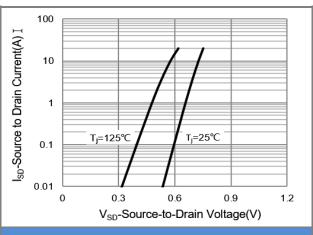


Fig.6 Source-Drain Diode Forward Voltage





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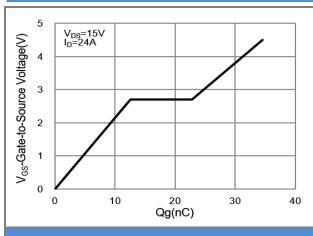


Fig.7 Gate-Charge Characteristics

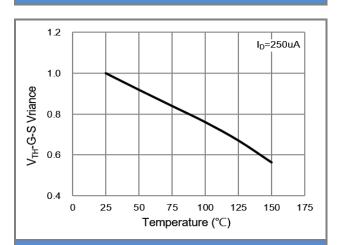
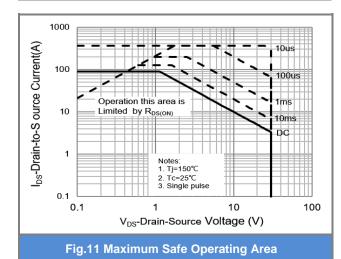


Fig.9 Threshold Voltage Variation with Temperature



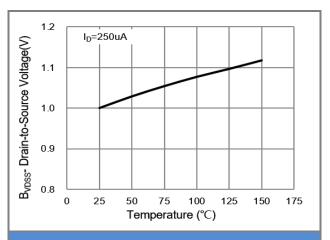


Fig.8 Breakdown Voltage Variation vs. Temperature

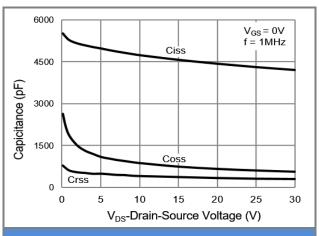


Fig.10 Capacitance vs. Drain-Source Voltage





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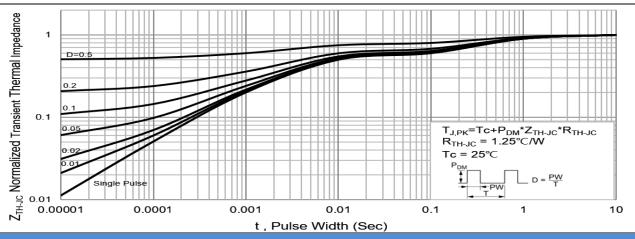
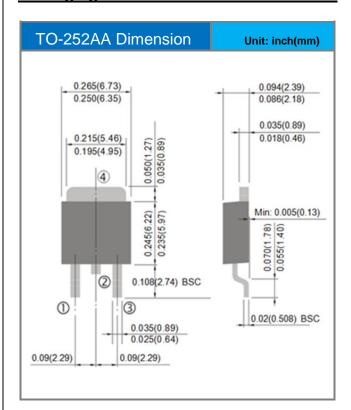


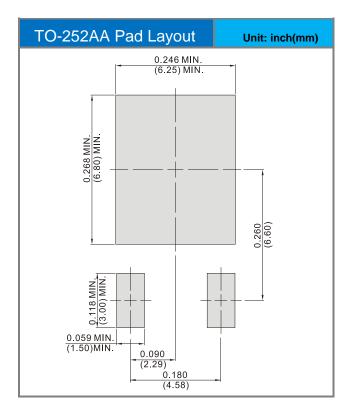
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





### **Packaging Information**









### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD90N03_L2_00001	TO-252AA	3,000pcs / 13" reel	D90N03	Halogen free	





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